

**UNIVERSITY OF CALIFORNIA BERKELEY**  
**Electrical Engineering and Computer Sciences**

**EE140/240A– MIDTERM #1**  
**Linear/Analog Integrated Circuits**

Instructor: Dr. Sashank Krishnamurthy

2024/02/16

Name: \_\_\_\_\_  
SID: \_\_\_\_\_

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This exam contains 20 pages (including this cover page) and 5 questions. Total of points is 52. Please write out the final answers to the questions in the boxes adjacent to the questions. Please show all your work in the space provided to work out the problems. Final answers without any work will not be given any credit.

For all the problems in this exam, assume  $\mu_n C_{ox} = 0.5 \text{mA/V}^2$ ,  $V_{Tn} = 0.3 \text{V}$  for the NMOS transistors. Assume  $\mu_p C_{ox} = 0.4 \text{mA/V}^2$ ,  $V_{Tp} = 0.45 \text{V}$  for the PMOS transistors. Also, assume that the channel length modulation parameter  $\lambda = 0$ , unless otherwise stated. Numbers adjacent to the MOS transistors indicate the (W/L) ratio of the transistors. Assume all capacitors are infinite, unless otherwise stated.

**Distribution of Points**

Question	Points	Score
1	12	
2	10	
3	13	
4	11	
5	6	
Total:	52	

1. In this question, we will work with a new device, whose characteristic is shown in Fig. 1

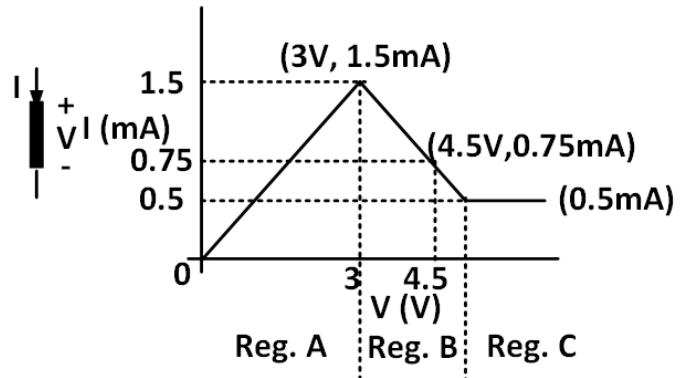
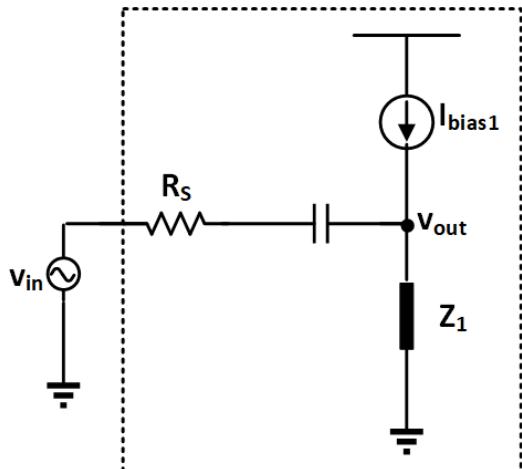


Figure 1: On the left is the circuit for Prob. 1 (a) - 1(c). On the right is the characteristic of the device used for all sub-parts of Prob. 1.

- (a) (1 point) In the circuit in Fig. 1, the desired small-signal gain from  $v_{in}$  to  $v_{out}$  is -2. In what region should we bias the element  $Z_1$ ?

- (b) (3 points) What should the value of  $R_S$  be to achieve this small-signal gain of -2?

- (c) (4 points) Under the bias condition of part (a) and  $R_S$  calculated in part (b), calculate the small-signal 2-port y-parameters for the circuit in the dashed box.

- (d) (4 points) Consider the circuit in Fig. 2. Assume that  $Z_1$  is biased in region B,  $Z_2$  is biased in region A, and  $R_S$  has the same value as what was computed in part (b). Under this bias condition, what is the small-signal gain  $v_{in}$  to  $v_{out}$ ?

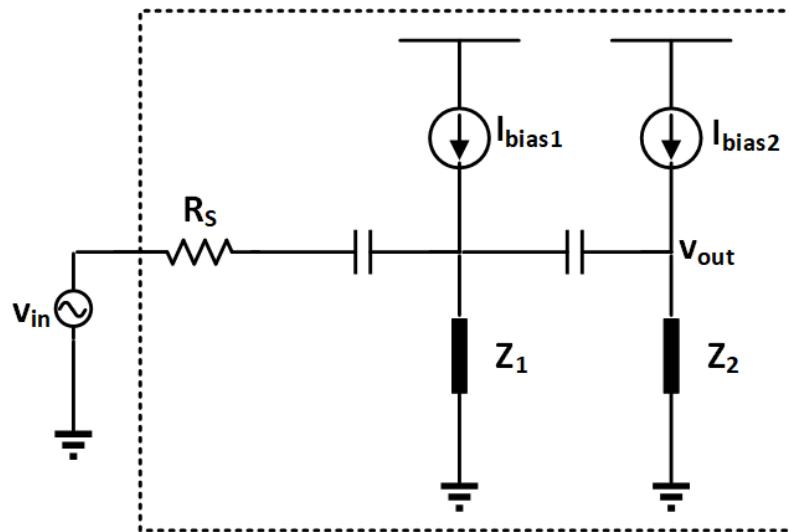


Figure 2: Prob. 1 (d)

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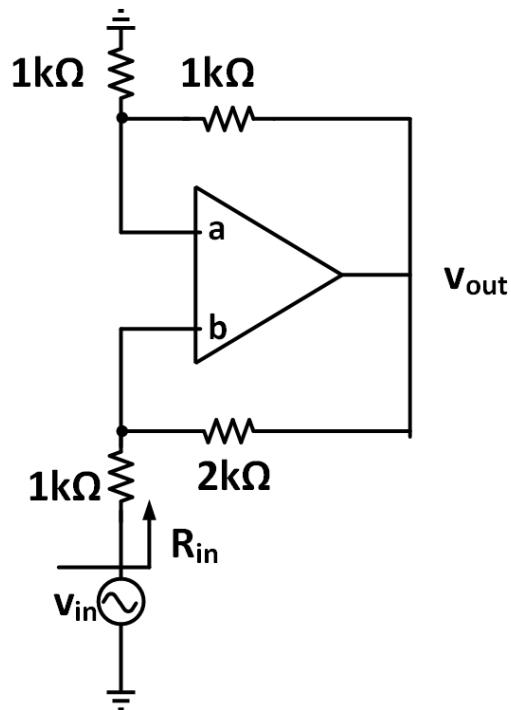


Figure 3: Prob. 2

2. (a) (3 points) Identify the signs on terminal (a) and (b) for the op-amp based circuit in Fig. 3 to be in negative feedback.

- (b) (3 points) Assuming that the op-amp is ideal, compute the gain  $v_{out}/v_{in}$ .

- (c) (4 points) Find the input resistance  $R_{in}$  looking into the circuit.

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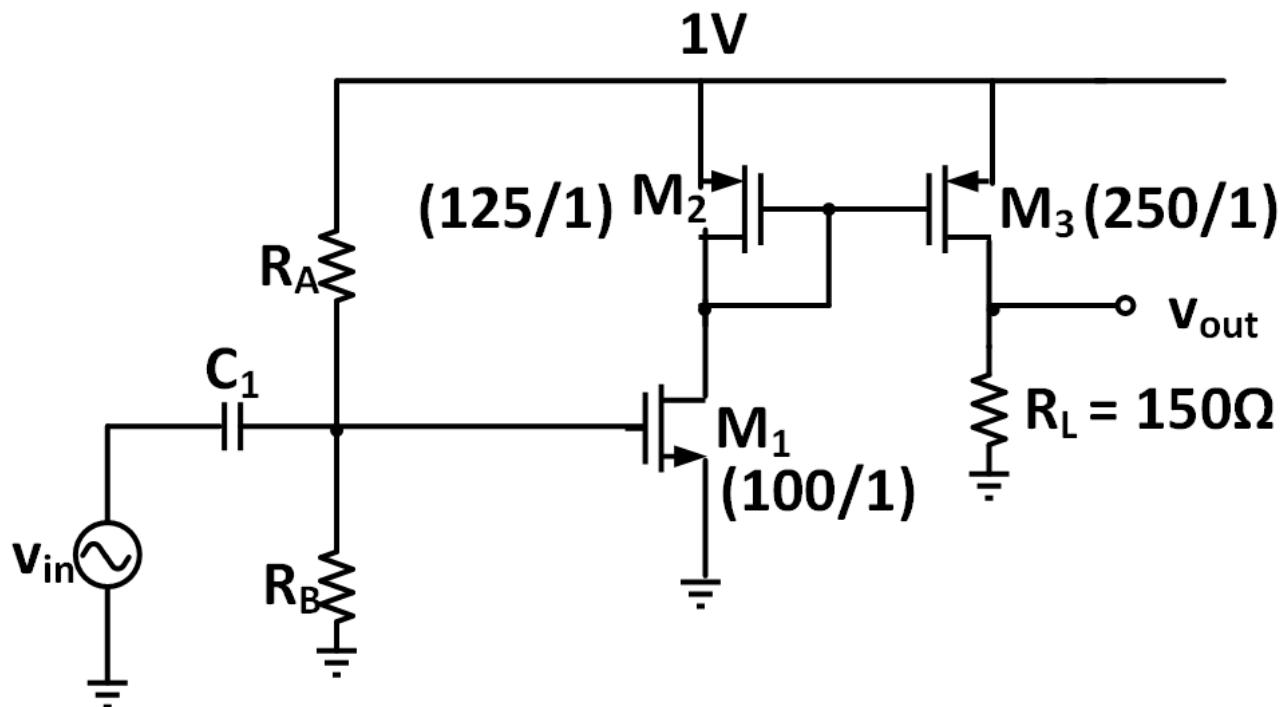


Figure 4: Prob. 3

3. (a) (4 points)  $C_1 = \frac{10}{2\pi} \text{nF}$ . Find the values of  $R_A$ ,  $R_B$  such that the drain current through  $M_1$  and  $M_2$  is 1mA, and the frequency associated with charging/discharging  $C_1$  is 10 times lower than the minimum input frequency of 1kHz. Use the values of  $R_A$ ,  $R_B$  obtained here for subsequent parts.

- (b) (4 points) Compute the small-signal gain from  $v_{in}$  to  $v_{out}$ . In this part, you may assume  $C_1 = \infty$ .

- (c) (5 points) Assume that the input  $v_{in}$  is a sinusoid of the form  $A \sin(\omega_0 t)$ . What is the maximum amplitude  $A$  such that all transistors remain in saturation? What limits the maximum swing?

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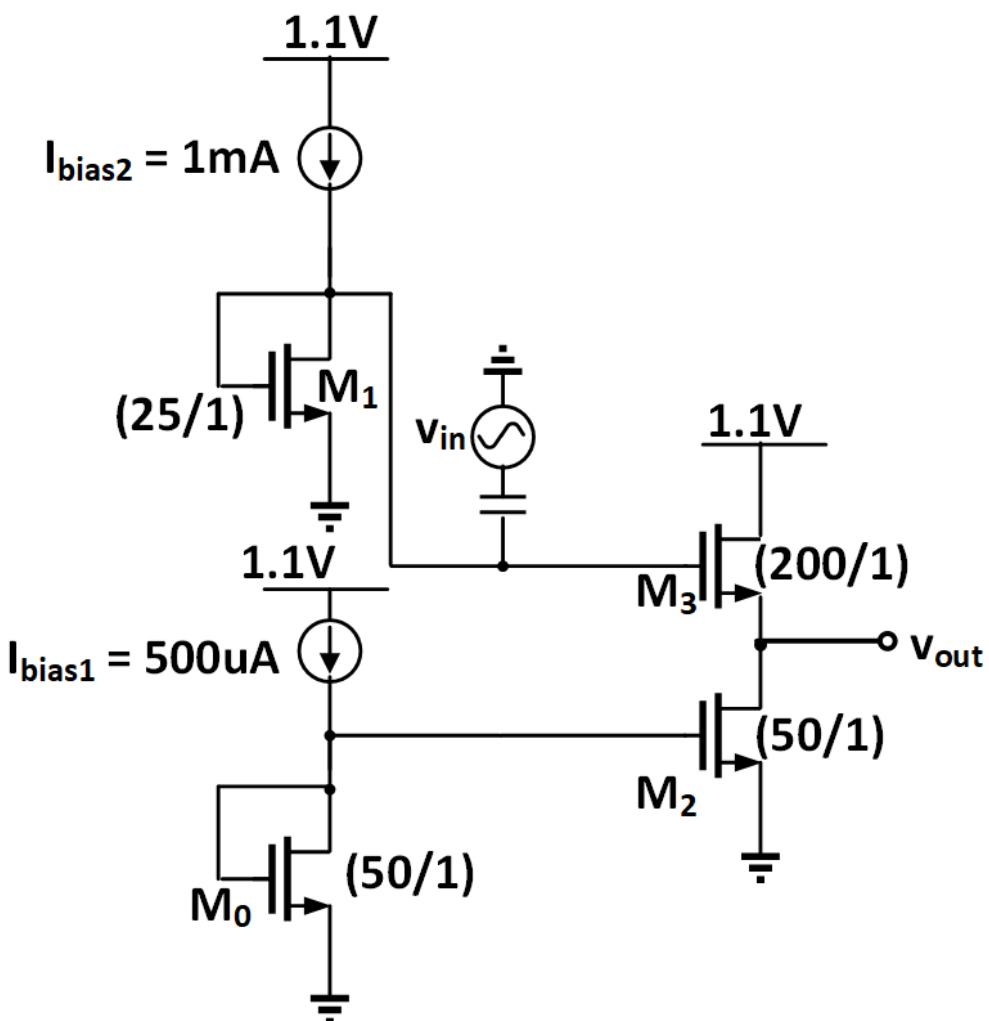


Figure 5: Prob. 4

4. (a) (4 points) Compute the DC operating point of the circuit shown in Fig. 5. That is calculate the DC voltage at the node  $v_{out}$ , gate voltages of  $M_2$  and  $M_3$  and the drain current through  $M_2$  and  $M_3$ .

- (b) (3 points) Compute the small-signal gain from  $v_{in}$  to  $v_{out}$ .

- (c) (4 points) Assume that the input  $v_{in}$  is a sinusoid of the form  $A\sin(\omega_0 t)$ . What is the maximum amplitude A such that all transistors remain in saturation? What limits the maximum swing?

Space to work out problem 4.

Space to work out problem 4.

Space to work out problem 4.

5. (6 points) The circuit shown in Fig. 6 is biased such that all transistors  $M_1, M_2, M_3$  are in saturation. The small-signal  $g_m$  and  $r_o$  of the transistors  $M_1, M_2, M_3$  are given by  $g_{m1}, r_{o1}, g_{m2}, r_{o2}, g_{m3}, r_{o3}$ , respectively. Calculate the output resistance  $R_{out}$  in terms of the small-signal parameters of the transistors  $g_{m1}, r_{o1}, g_{m2}, r_{o2}, g_{m3}, r_{o3}$ . You may assume  $g_m r_o \gg 1$  for all transistors.  $V_{G1}, V_{G2}$  and  $V_{G3}$  are the DC bias voltages for  $M_1, M_2, M_3$  respectively.

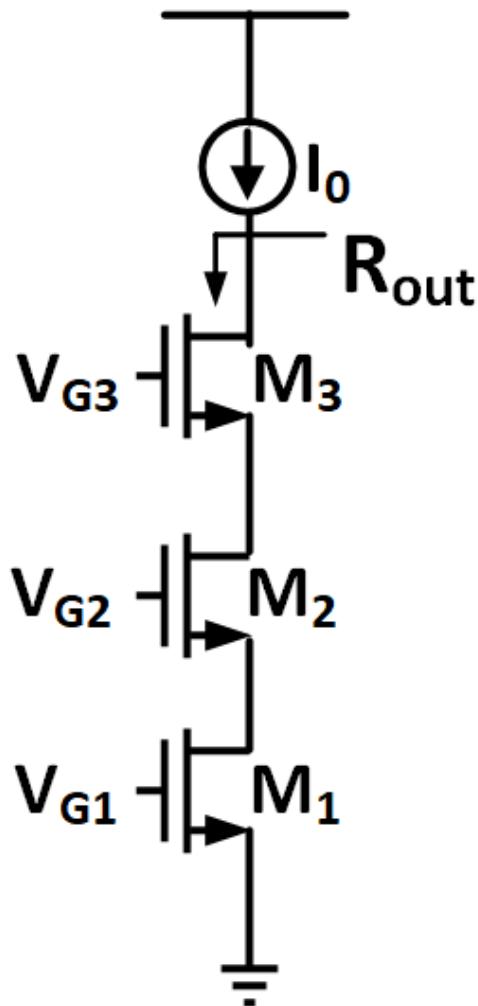


Figure 6: Prob. 5

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